

General Description

The 11N43 have been fabricated using an advanced high voltage MOSFET process. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

Features

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS Compliant

Product Summary

BVDSS	RDSON	ID
430V	0.5Ω	11A

Applications

- Power Supply
- PFC

TO-252 / 251 Pin Configuration



Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DSS}	Drain-Source Voltage	430	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	11	A
		6.6	A
I _{DM}	Drain Current - Pulsed (Note 1)	44	A
V _{GSS}	Gate-Source Voltage	±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	484	mJ
P _D	Power Dissipation (T _C = 25°C)	100	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Rating	Units
R _{θJC}	Thermal Resistance, Junction-to-Case Max. (Note 3,4)	1.2	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient Max. (Note 5,6)	62.5	°C/W

Electrical Characteristic (T_c=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	430	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400 V, V _{GS} = 0 V	--	--	1	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = +30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	--	4	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 5.5A	--	--	0.5	Ω
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 5.5A	--	10	--	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1100	--	pF
C _{oss}	Output Capacitance		--	120	--	pF
C _{rss}	Reverse Transfer Capacitance		--	12	--	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{DD} = 200 V, I _D = 11A, R _G = 25 Ω	--	15	--	ns
t _r	Turn-On Rise Time		--	90	--	ns
t _{d(off)}	Turn-Off Delay Time		--	80	--	ns
t _f	Turn-Off Fall Time		--	80	--	ns
Q _g	Total Gate Charge	V _{DS} = 320 V, I _D = 11A, V _{GS} = 10 V	--	30	--	nC
Q _{gs}	Gate-Source Charge		--	5	--	nC
Q _{gd}	Gate-Drain Charge		--	15	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	11	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	44	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 11A	--	--	1.2	V

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L=8mH , I_{AS}=11A , V_{DD}=50V , Starting T_J=25 °C
- 3.The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- 4.These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150 °C .
- 5.The value of R_{θJA} is measured with the device in a still air environment with T_A=25 °C .
- 6.These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C .

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